

FIG. 1

Growth parameters and characterization results of Samples A-D

	Sample A	Sample B	Sample C	Sample D
Final Ge composition	100%	100%	50%	100%
Grading rate (%Ge µm ⁻¹)	5	10	10	10
Total epitaxial thickness (µm)	23	12	6.5	12
Growth temperature (°C)	750	800	750	50-76%: 750 76-100%: 550
Growth pressure (mT)	25	50	25	50-76%: 25 76-100%: 3
CMP at 50%	No	No		Yes
Threading dislocation density (cm ⁻²)	1±0.1×10 ⁷	1-5×10 ⁷	6.3±0.1×10 ⁶	2.1±0.2×10 ⁶
Crack density (cm ⁻¹)	47±5	0	0	0
Particle density (cm ⁻²)	1250±100	600±40	50±5	150±10
RMS roughness (nm)	35.9	47	37.3	24.2
a _⊥ of top layer (Å)	5.6559	5.6558	5.5327	5.6597
all of top layer (Å)	5.6559	5.6552	5.5352	5.6409

FIG. 2

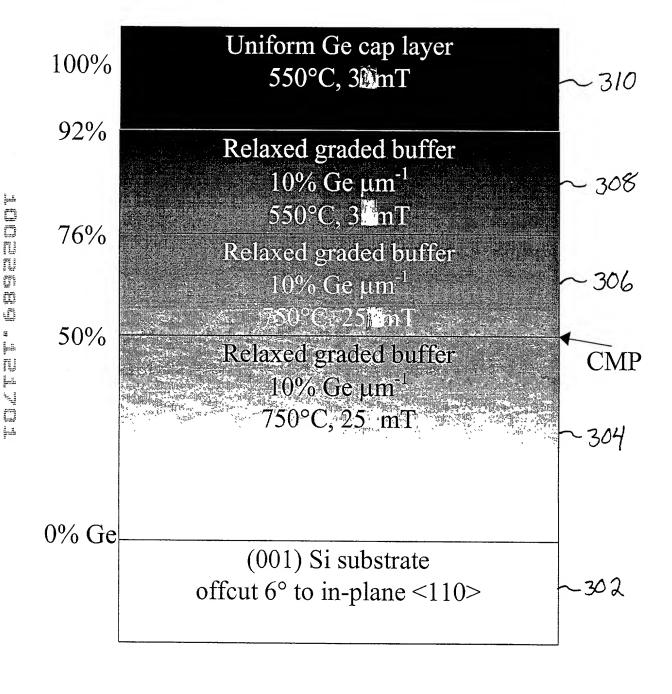


FIG. 3



FIG. 4

FIG.5A

